Desert Silicon
LIQUID SOURCE SOLUTIONS

# Spin-on-Glass GaB-220

| Elements of Interest | Key Element atoms/cm$^3$ | Key Element % in Film |
|---|---|---|
| Si, O, Ga, B | Ga, 4E+21, B, 9.4E+21 | Gallium, Boron |
| **Viscosity, n (635nm)** | **Thickness** | **Shelf Life** |
| 1.0 cps, 1.5 | Coats 270 nm at 3000 rpm | 20°C 3 months<br>4°C 9 months |

## Benefits

- Gallium, Boron mixture
- Uniform Coatings
- High purity materials
- Lower melting point than silica alone
- Stable processing independent of flow rates
- Available with impurity specification of less than 1 ppm or less than 50 ppb

## Typical Application

This is a mixture of silicate gallium and boron doped glass useful for semiconductor applications. It begins curing at about 200°C to give a less dense but solid film. It continues to become increasingly stronger as bakes continue to 650°C or higher. We recommend baking at the highest temperature the material will see in any post processing. For doping applications the glass is often removed after drive in.

## Packaging

- 240ml
- 500ml
- 1 l
- 2.5 l
- 4 l

## Alternative Products

- Ga-100
- B-1200

## Alternate Elements to Add

- Blends of two or more elements
- Other elements available for compound semiconductor use

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